2SD974

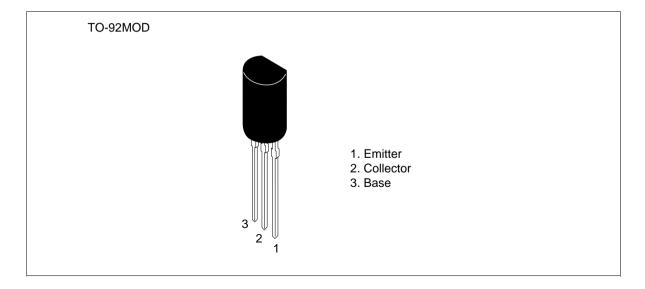
Silicon NPN Epitaxial

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Application

- Power switching
- TV horizontal deflection output

Outline





2SD974

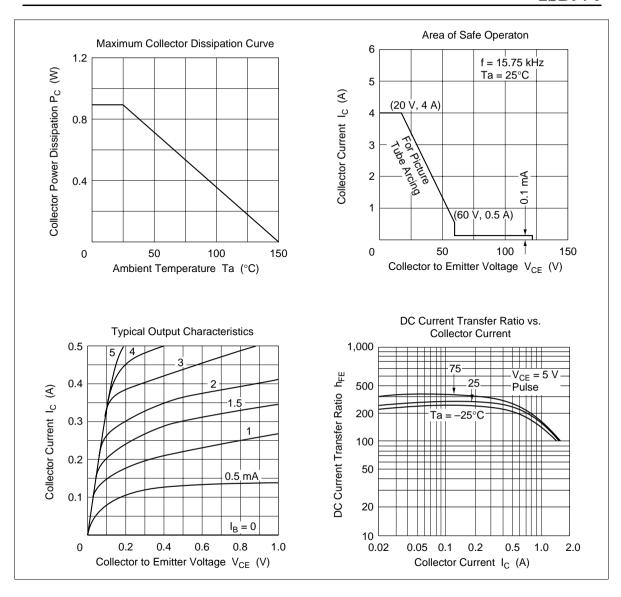
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	120	V
Collector to emitter voltage	V _{CEO}	60	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	1	A
Collector peak current	i _{C(peak)}	1.5	A
Surge collector current	I _{C(surge)}	4	A
Collector power dissipation	P _c	0.9	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

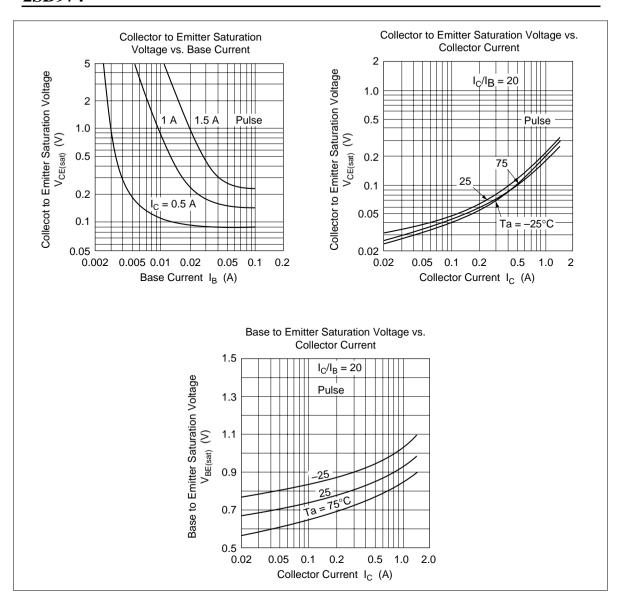
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	_	_	V	$I_{c} = 10 \ \mu A, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	60	_	_	V	I_{C} = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	1.0	μΑ	V _{CB} = 100 V, I _E = 0
DC current transfer ratio	h _{FE}	150	_	_		$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.3	V	$I_{\rm C} = 1 \text{ A}, I_{\rm B} = 0.05 \text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	1.2	MHz	_
Fall time	t _f	_	0.4	_	pF	$I_{CP} = 1 \text{ A}, I_{B1} = -I_{B2} = 50 \text{ mA}^{*1}$

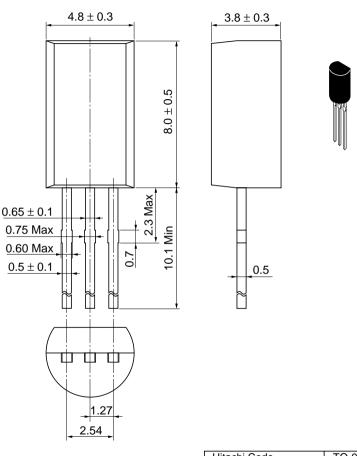
Note: 1. Pulse test



2SD974



Unit: mm



Hitachi Code TO-92 Mod

JEDEC —

EIAJ Conforms

Weight (reference value) 0.35 g

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